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RLT1060-10G TECHNICAL DATA



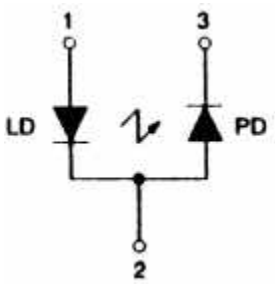
High Power Infrared Laserdiode

Structure: **QW structure**
Lasing wavelength: **1060 nm typ.**
Lasing Aperture: **1.5 x 3 μm^2**
Max. optical power: **10 mW, single mode**
Package: **9 mm**

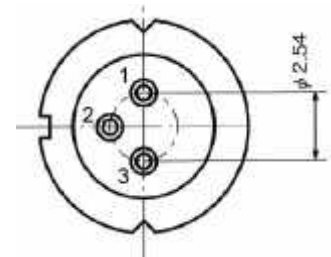
NOTE!
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode anode
- 2) Laser diode cathode and photodiode anode
- 3) Photodiode cathode



Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	12	mW
LD Reverse Voltage	V _{R(LD)}	1.5	V
PD Reverse Voltage	V _{R(PD)}	6	V
Operating Temperature	T _c	-60 .. +60	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw		10		mW
Threshold Current	I _{th}	cw		10		mA
Operation Current	I _{op}	P _o = 10 mW		50		mA
Forward Voltage	U _f	P _o = 10 mW		2.0		V
Lasing Wavelength	λ_p	P _o = 10 mW		1060		nm
Spectral Width (FWHM)	$\Delta\lambda$	P _o = 10 mW		2.0		nm
Beam Divergence	$\theta_{//}$	P _o = 10 mW		10		°
Beam Divergence	$\theta_{\perp}$	P _o = 10 mW		40		°
Differential Efficiency	dP _o /dI _{op}	P _o = 10 mW		0.2		mW/mA
Monitor Current	I _m	P _o = 10 mW		40		μA